[Claims]

[Claim 1]

Etchant composition for batch etching treatment of tungsten film and titanium nitride film comprising a nitric acid, ~~and~~ water, a phosphoric acid and at least one selected from the group consisting of a sulfuric acid and an aliphatic sulfonic acid, wherein the sulfuric acid is in an amount between 11.73 and 40.0 wt % and the aliphatic sulfonic acid is in an amount between 17.71 and 40.0 wt%.

~~[Claim 2]~~

~~The etchant composition according to Claim 1, further comprising at least one selected from the group consisting of asulfuric acid and an aliphatic sulfonic acid.~~

[Claim ~~3~~2]

The etchant composition according to Claim ~~2~~1, wherein the ~~aliphatic sulfonic acid~~ etchant composition comprises~~is~~ a methanesulfonic acid.

~~[Claim 4]~~

~~The etchant composition according to any one of Claims 1 to 3further comprising a phosphoric acid.~~

[Claim ~~5~~3]

Method for batch etching of tungsten film and titanium nitride film using the etchant composition according to any one ofClaims 1 to ~~4~~2.

[Claim ~~6~~4]

The method according to Claim ~~5~~3, wherein the temperature of the etching composition at which the etching is performed is 50 ℃or higher.

[Claim ~~7~~5]

The method according to Claim ~~5~~ 3 or ~~6~~ 4 for generating a patternhaving a three-dimensional structure.